

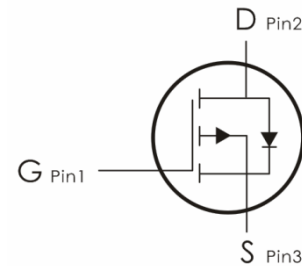
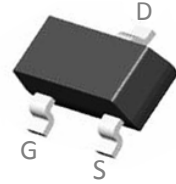
Description:

This P-Channel MOSFET uses advanced trench technology and design to provide excellent $R_{DS(on)}$ with low gate charge.

It can be used in a wide variety of applications.

Features:

- 1) $V_{DS}=-30V, I_D=-4.3A, R_{DS(ON)}<55m\Omega @V_{GS}=-10V$ (Typ: $37m\Omega$)
- 2) Low gate charge.
- 3) Green device available.
- 4) Advanced high cell density trench technology for ultra low $R_{DS(ON)}$.
- 5) Excellent package for good heat dissipation.
- 6) MSL3



Package Marking and Ordering Information:

Part NO.	Marking	Package	Packing
DO3407BA	3407B	SOT-23-3	3000pcs/Reel

Absolute Maximum Ratings: ($T_A=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Ratings	Units
V_{DS}	Drain-Source Voltage	-30	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Continuous Drain Current	-4.3	A
I_{DM}	Drain Current-Pulsed ¹	-17.2	A
P_D	Power Dissipation	1.51	W
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ\text{C}$

Thermal Characteristics:

Symbol	Parameter	Max	Units
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient ²	83	$^\circ\text{C}/\text{W}$

Electrical Characteristics: ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
Off Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250 μ A	-30	-33	---	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{GS} =0V, V _{DS} =-30V	---	---	-1	μ A
I _{GSS}	Gate-Source Leakage Current	V _{GS} =± 20V, V _{DS} =0A	---	---	± 100	nA
On Characteristics						
V _{GS(th)}	Gate -Source Threshold Voltage	V _{GS} =V _{DS} , I _D =-250 μ A	-1	-1.5	-3	V
R _{DS(ON)}	Drain-Source On Resistance ³	V _{GS} =-10V, I _D =-4 A	---	37	55	m Ω
		V _{GS} =-4.5V, I _D =-3A	---	50	70	
G _{FS}	Forward Transconductance	V _{DS} =-5V, I _D =-1A	---	10	---	S
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =-15V, V _{GS} =0V, f=1MHz	---	490	---	pF
C _{oss}	Output Capacitance		---	65	---	
C _{rss}	Reverse Transfer Capacitance		---	58	---	
Switching Characteristics						
t _{d(on)}	Turn-On Delay Time	V _{DD} =-15V, R _L =3.6Ω V _{GS} =-10V, R _{GEN} =3Ω	---	3	---	ns
t _r	Rise Time		---	2	---	ns
t _{d(off)}	Turn-Off Delay Time		---	26	---	ns
t _f	Fall Time		---	14.5	---	ns
Q _g	Total Gate Charge	V _{GS} =-10V, V _{DS} =-15V, I _D =-4 A	---	7	---	nC
Q _{gs}	Gate-Source Charge		---	2.2	---	nC
Q _{gd}	Gate-Drain Charge		---	2.1	---	nC
Drain-Source Diode Characteristics						
V _{SD}	Diode Forward Voltage	V _{GS} =0V, I _{SD} =-4.3A	---	---	-1.2	V
I _S	Continuous Drain Curren	V _D =V _G =0V	---	---	-4.3	A
I _{SM}	Pulsed Drain Current		---	---	-17	A

Notes:

1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.
2. $R_{\theta JA}$ is measured with the device mounted on a 1inch² pad of 2oz copper FR4 PCB
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 0.5\%$.

Typical Characteristics: ($T_A = 25^\circ C$ unless otherwise noted)

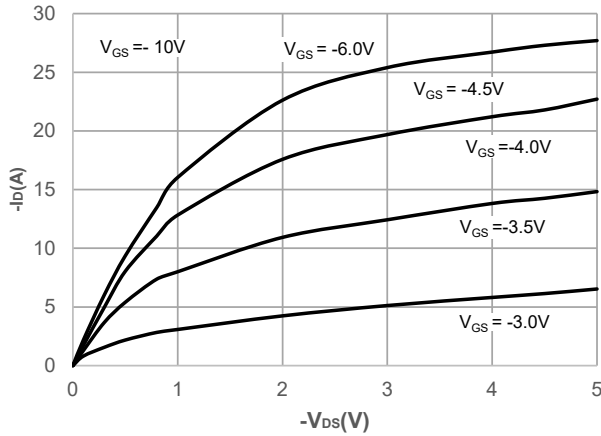


Figure 1: Output Characteristics

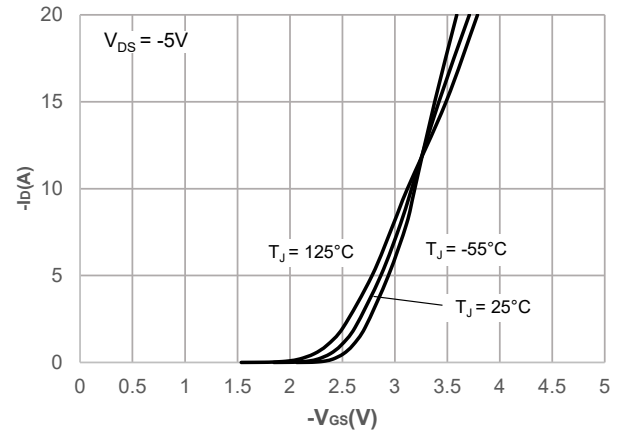


Figure 2: Typical Transfer Characteristics

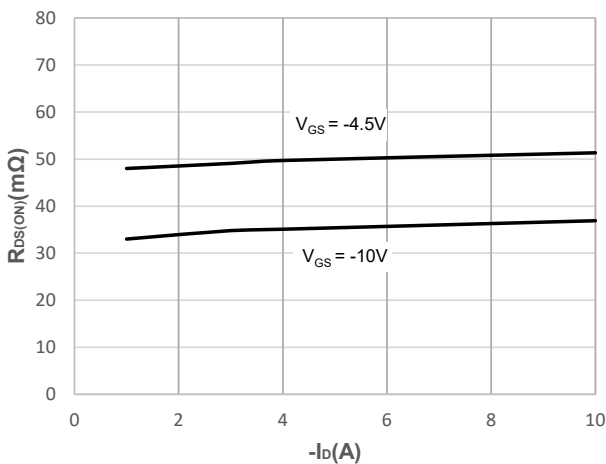


Figure 3: On-resistance vs. Drain Current

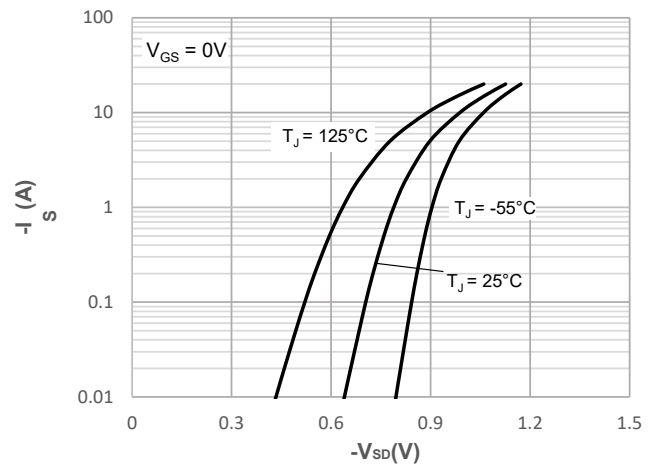


Figure 4: Body Diode Characteristics

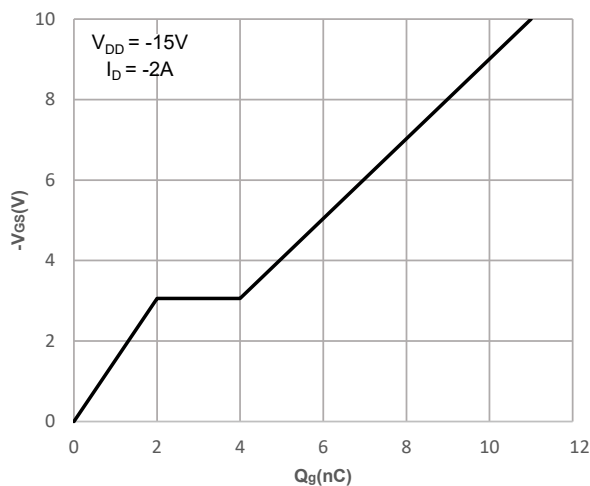


Figure 5: Gate Charge Characteristics

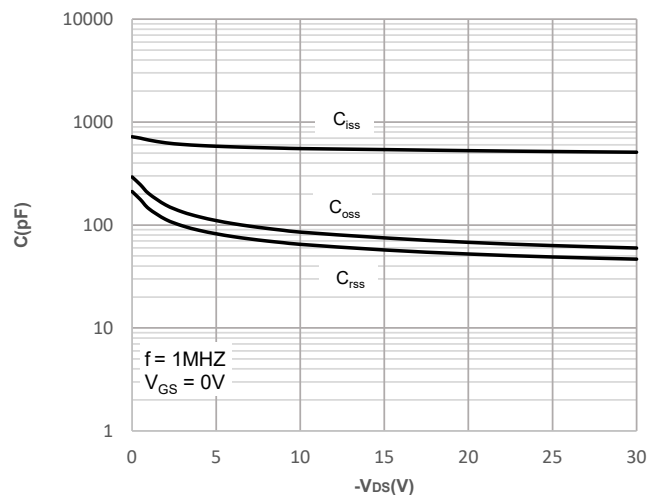


Figure 6: Capacitance Characteristics

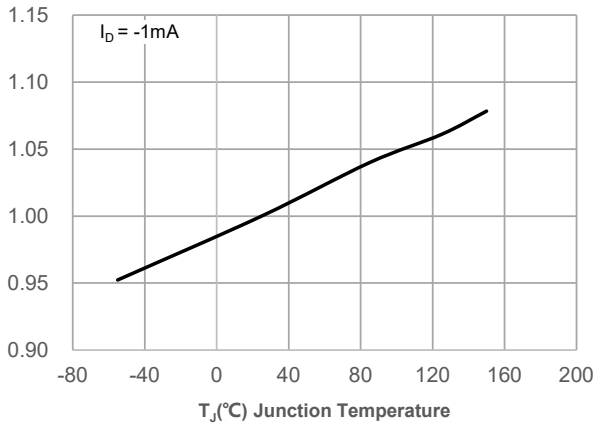


Figure 7: Normalized Breakdown voltage vs. Junction Temperature

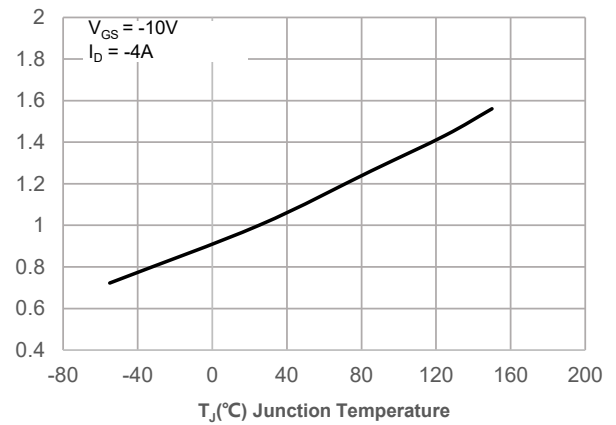


Figure 8: Normalized on Resistance vs. Junction Temperature

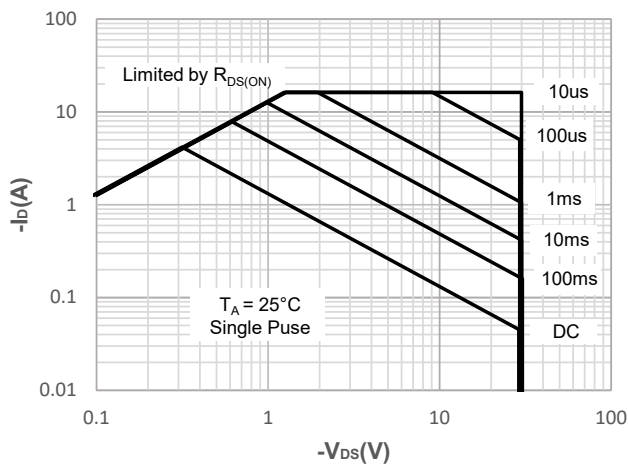


Figure 9: Maximum Safe Operating Area

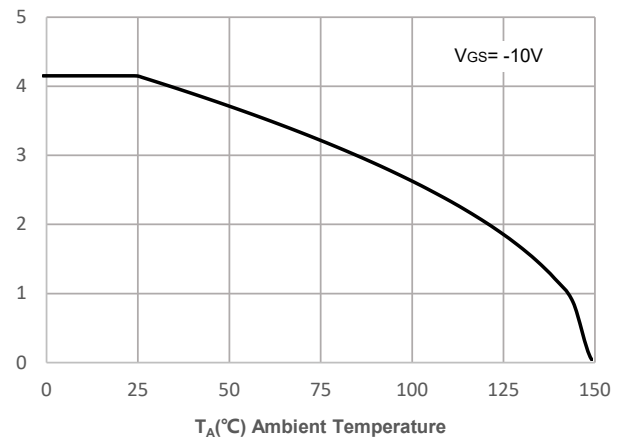


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

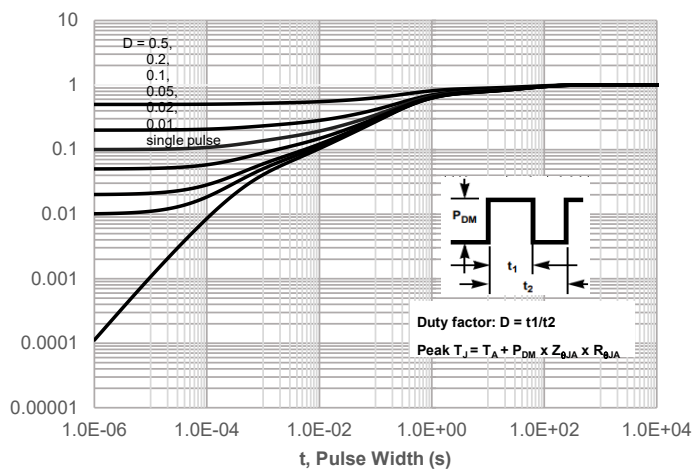


Figure 11: Normalized Maximum Transient Thermal Impedance

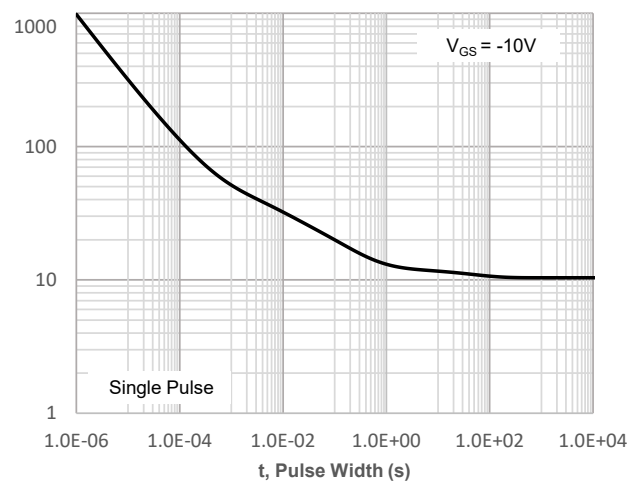
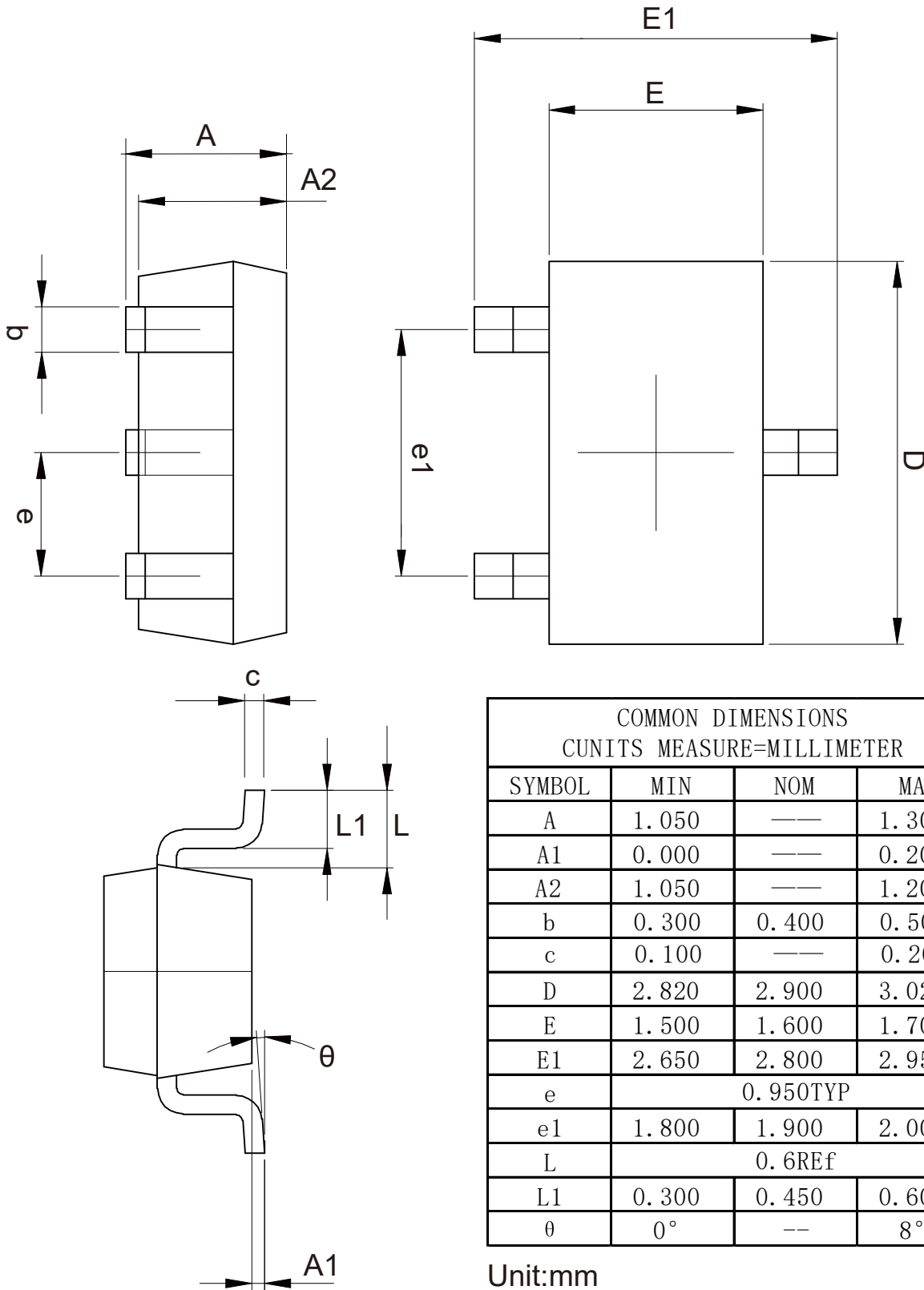


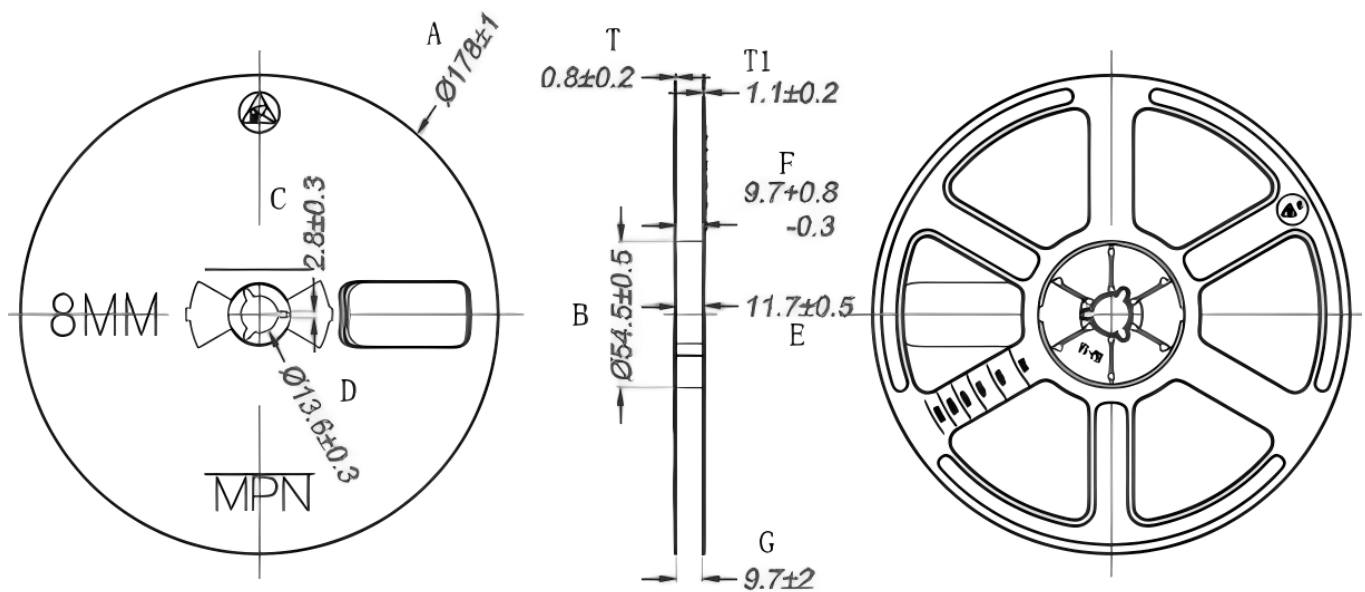
Figure 12: Peak Current Capacity

SOT-23-3 PackageOutlineData

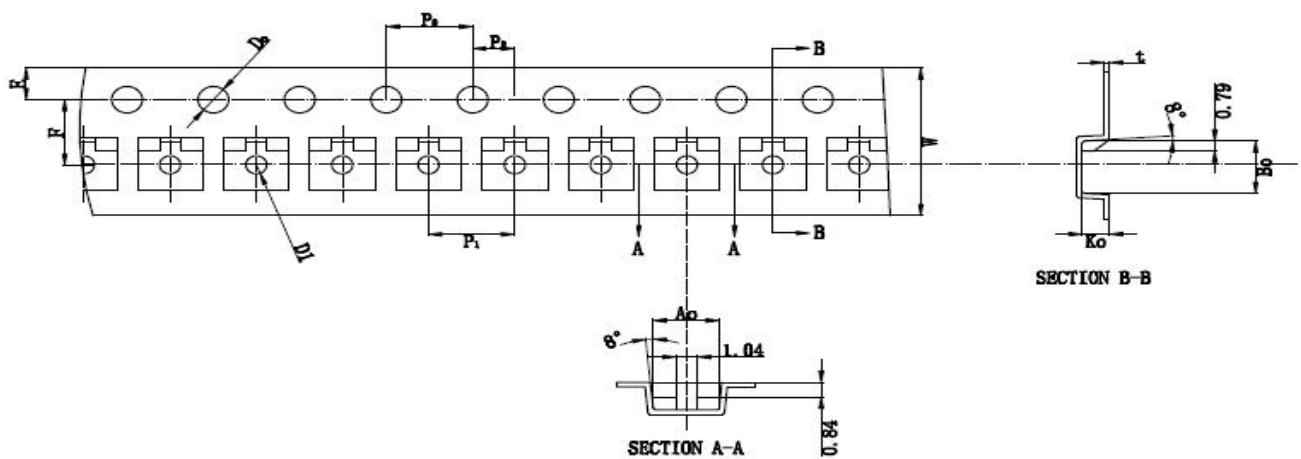


Tape & Reel Information

Dimensions in mm

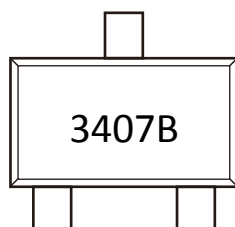


PKG TYPE	W	P	E	F	D	D1	Po	Po10	P2	A0	B0	K0	T
SOT23-3	8.00	4.00	1.75	3.50	1.50	1.00	4.00	40.00	2.00	3.13	3.22	1.30	0.20
Tolerance	± 0.2	± 0.1	± 0.1	± 0.1	± 0.1	± 0.1	± 0.1	± 0.2	± 0.1	± 0.1	± 0.1	± 0.1	± 0.03



Pulling direction 

Marking Information:



Previous Version

Version	Date	Subjects (major changes since last revision)
2.2	2026-02-06	Release of final version

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